

ZrO<sub>2</sub>-WO<sub>3</sub> Mixed Anodic Oxide Nanotubular Arrays as Electrochemical Capacitors

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Vertically oriented, ordered arrays of oxide nanotubes, such as TiO<sub>2</sub>, WO<sub>3</sub>, and Fe<sub>2</sub>O<sub>3</sub> are considered for electrochemical capacitor application because of their morphology-assisted fast charge/discharge kinetics and large surface area.<sup>1,2</sup> Recently, Habazaki et al<sup>3</sup> reported enhanced capacitance of anodic ZrO<sub>2</sub> film by stabilizing the high permittivity tetragonal phase in a highly resistive amorphous oxide phase containing Al or Si. In this presentation, electrochemical capacitance of a binary ZrO<sub>2</sub>-WO<sub>3</sub> oxide nanotubular arrays will be discussed.

ZrO<sub>2</sub>-WO<sub>3</sub> mixed oxide nanotubes were synthesized by a simple electrochemical anodization of the Zr- 20 wt%W alloy substrate. Figures 1(a) – (c) show the morphology of the nanotubes. The as-anodized oxide nanotubes contained a mixture of metastable hexagonal WO<sub>3</sub> and monoclinic ZrO<sub>2</sub> phases. A mixed-oxide ZrW<sub>2</sub>O<sub>8</sub> phase with a metastable tetragonal symmetry formed after thermal annealing the nanotubes. Formation of h-WO<sub>3</sub> and mixed oxide phase of ZrW<sub>2</sub>O<sub>8</sub> was supported by both XRD and XPS data. Presence of the h-WO<sub>3</sub> in the nanotubes was considered critical for the enhancement of the capacitance because its ring like lattice structure containing hexagonal tunnels at the center of the rings that accommodated intercalation ions.

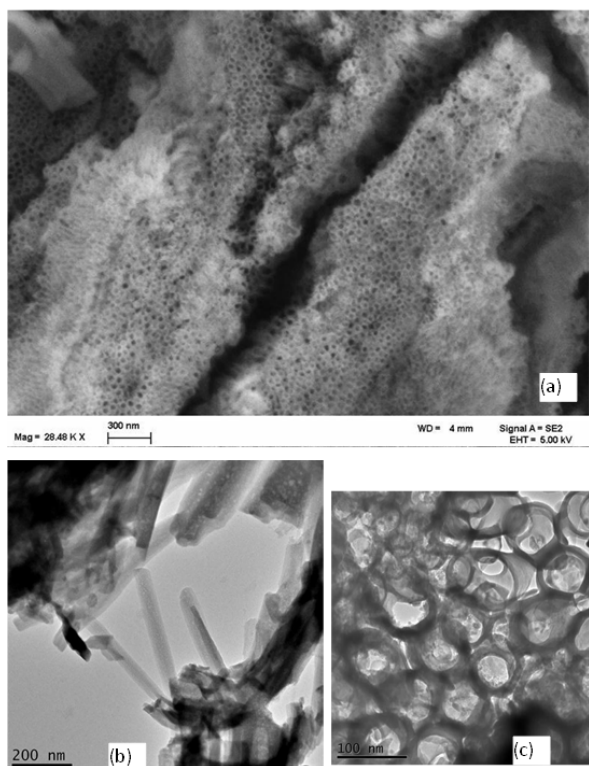


Figure 1: Electron microscopic images of oxide layers formed on the Zr-W alloy substrate after anodization at 40 V for 1 h in EG electrolyte containing 0.2 M NH<sub>4</sub>F + 5 vol% H<sub>2</sub>O. (a) FESEM image of the top surface of the anodic oxide layer revealing nanotubular morphology; (b) TEM image of the side view of the nanotubes; and (c) planar view of the nanotubes under TEM.

Cyclic voltammetry studies were carried out in 1 M H<sub>2</sub>SO<sub>4</sub> and 1 M LiCl solution to evaluate the electrochemical capacitance of the nanotubes. Electrochemical impedance spectroscopy and Mott-

Schottky measurements were carried out to determine the charge transfer resistance and defect concentration of the nanotubes, respectively. Figures 2(a) and (b) show typical cyclic voltammograms of the Zr-W oxide nanotubes in 1 M H<sub>2</sub>SO<sub>4</sub> at different scan rates. The highest measured capacitance was 1900 μF/cm<sup>2</sup> at a scan rate of 100 mV/s and the lowest was 400 μF/cm<sup>2</sup> at 1 V/s in 1 molar sulfuric acid solution. This capacitance was comparable to that reported for the ordered mesoporous WO<sub>3</sub> material and higher than the capacitance reported for the TiO<sub>2</sub> nanotubes (181 μF/cm<sup>2</sup> at 100 mV/s).

The higher capacitance of Zr-W oxide nanotubes could be attributed to the distribution of high dielectric h-WO<sub>3</sub> and ZrW<sub>2</sub>O<sub>8</sub> phases in the ZrO<sub>2</sub> matrix, presence of high concentration of oxygen vacancies (in the order of 10<sup>21</sup> cm<sup>-3</sup>), and high proton conductivity of the mixed ZrO<sub>2</sub>-WO<sub>3</sub> oxide reported in the literature.

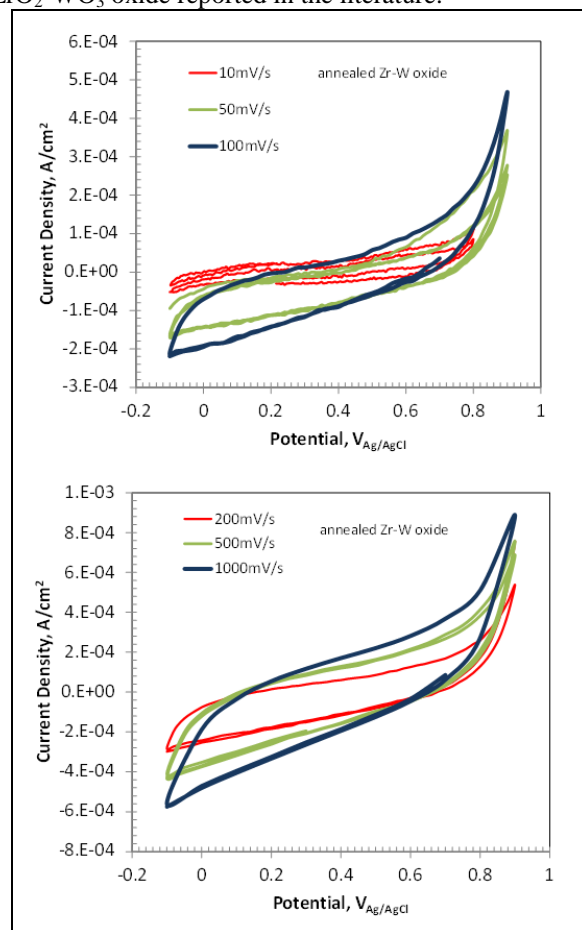


Figure 2: (a) Representative cyclic voltammetry (CV) results of annealed Zr-W oxide nanotubes (anodized for 1 h) tested in 1 M H<sub>2</sub>SO<sub>4</sub> solution at three different scan rates 10, 50, and 100 mV/s. The results of 50<sup>th</sup>, and 100<sup>th</sup> cycles are shown. (b) Representative cyclic voltammetry (CV) results of annealed Zr-W oxide nanotubes (anodized for 1 h) tested in 1 M H<sub>2</sub>SO<sub>4</sub> solution at three different scan rates 200, 500, and 1000 mV/s. The results of 50<sup>th</sup>, and 100<sup>th</sup> cycles are shown.

<sup>1</sup> Salari, M.; Aboutalebi, S.H.; Konstantinov, K.; Liu, H. K. *Phys. Chem. Chem. Phys.* **2011**, 13, 5038-5041.

<sup>2</sup> Lee, K. K.; Deng, S.; Fan, H. M.; Mhaisalkar, S.; Tan, H. R.; Tok, E. S.; Loh, K. P.; Chin, W. S.; Sow, C. H. *Nanoscale.* **2012**, 4, 2958-2961.

<sup>3</sup> H. Habazaki, S. Koyama, Y. Aoki, N. Sakaguchi, S. Nagata, *ACS Appl. Mater. Interfaces* **2011**, 3, 2665–2670